DERWENT-ACC-NO: 2002-289444

DERWENT-WEEK: 200233

TITLE: Non-volatile memory device and method for manufacturing the same

INVENTOR: RA, G Y

PRIORITY-DATA: 1999KR-0043852 (October 11, 1999)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE	PAGES	MAIN-IPC
KR 2001036727 A	May 7, 2001	N/A	001	H01L 027/115

INT-CL (IPC): H01L027/115

ABSTRACTED-PUB-NO: KR2001036727A

BASIC-ABSTRACT:

NOVELTY - A non-volatile memory device and a method for manufacturing the same
are provided to improve the program efficiency of a memory device by generating
thermoelectrons from a source region.

DETAILED DESCRIPTION - A gate insulating layer(22) is formed on a
substrate(21). A floating gate(23) is formed on the gate insulating layer(22).
A conductive sidewall(25) is formed at one side of the floating gate(23). An
ONO(Oxide-Nitride-Oxide) layer(29) is formed on a whole face of the
substrate(21) including the conductive sidewall(25) and the floating gate(23).
A control gate(30) is formed on the ONO layer(29). A source region(26) is

formed on a surface of the substrate(21) of the conductive sidewall(25). A
drain region(27) is formed on a surface of the substrate(21) corresponding to
the source region(26).

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